



# 650V Super-Junction Power MOSFET

## DESCRIPTION

### 650V Super-junction Power MOSFET

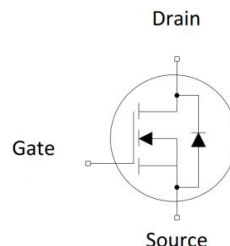
Super-junction power MOSFET is a revolutionary technology for high voltage power MOSFETs, designed according to the SJ principle and pioneered. The Multi-EPI SJ MOSFET provide an extremely fast and robust body diode. Also provide an extremely low switching, communication and conduction losses device with highest robustness make especially resonant switching applications more reliable, more efficient, lighter and cooler, designed by Wuxi Unigroup Microelectronics Company.

## FEATURES

- Ultra-fast body diode
- Very low FOM  $R_{DS(on)} \times Q_g$
- Easy to use/drive
- 100% avalanche tested
- RoHS compliant

## APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)
- LLC Half-bridge
- Charger



## Device Marking and Package Information

Device	Package	Marking
TPA65R400MFD	TO-220F	65R400MFD

## Key Performance Parameters

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	650	V
$R_{DS(on),max}$	0.40	$\Omega$
$I_D$	11	A
$Q_{g,typ}$	21	nC
$I_{DM}$	33	A
$t_{rr}$	120	ns
$Q_{rr}$	0.56	$\mu$ C
$I_{rrm}$	9.3	A



<b>Absolute Maximum Ratings</b> $T_C = 25^\circ\text{C}$ , unless otherwise noted			
Parameter	Symbol	Value	Unit
Drain-Source Voltage ( $V_{GS} = 0\text{V}$ )	$V_{DSS}$	650	V
Continuous Drain Current	$I_D$	$T_C = 25^\circ\text{C}$	11
		$T_C = 100^\circ\text{C}$	6.6
Pulsed Drain Current (note1)	$I_{DM}$	33	A
Gate-Source Voltage	$V_{GSS}$	$\pm 30$	V
Single Pulse Avalanche Energy (note2)	$E_{AS}$	215	mJ
Repetitive Avalanche Energy (note2)	$E_{AR}$	0.32	mJ
Avalanche Current	$I_{AR}$	1.8	A
MOSFET dv/dt ruggedness, $V_{DS} = 0 \dots 480\text{V}$	dv/dt	50	V/ns
Power Dissipation	$P_D$	31	W
Continuous Body Diode Current	$I_S$	11	A
Pulsed Diode Forward Current (note1)	$I_{SM}$	33	
Reverse diode dv/dt (note3)	dv/dt	15	V/ns
Maximum diode commutation speed (note3)	$di_f/dt$	500	A/us
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55~+150	$^\circ\text{C}$

<b>Thermal Resistance</b>			
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{thJC}$	4	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	$R_{thJA}$	80	



Specifications $T_J = 25^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	650	--	--	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 650V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1.25	$\mu A$
		$V_{DS} = 650V, V_{GS} = 0V, T_J = 150^\circ\text{C}$	--	--	1250	
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 30V$	--	--	$\pm 100$	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	3	--	5	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 5.5A$	--	0.35	0.40	$\Omega$
Gate resistance	$R_G$	$f = 1.0\text{MHz}$ open drain	--	18	--	$\Omega$
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0V,$ $V_{DS} = 100V,$ $f = 1.0\text{MHz}$	--	882	--	$\mu F$
Output Capacitance	$C_{oss}$		--	30	--	
Reverse Transfer Capacitance	$C_{rss}$		--	2	--	
Total Gate Charge	$Q_g$	$V_{DD} = 520V, I_D = 11A,$ $V_{GS} = 10V$	--	21	--	nC
Gate-Source Charge	$Q_{gs}$		--	6	--	
Gate-Drain Charge	$Q_{gd}$		--	9	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 400V, I_D = 11A,$ $R_G = 25\Omega$	--	27	--	ns
Turn-on Rise Time	$t_r$		--	24	--	
Turn-off Delay Time	$t_{d(off)}$		--	120	--	
Turn-off Fall Time	$t_f$		--	27	--	
<b>Drain-Source Body Diode Characteristics</b>						
Body Diode Voltage	$V_{SD}$	$T_J = 25^\circ\text{C}, I_{SD} = 5.5A, V_{GS} = 0V$	--	1.0	1.5	V
Reverse Recovery Time	$t_{rr}$	$V_R = 400V, I_F = I_S,$ $di_F/dt = 100A/\mu s$	--	120	--	ns
Reverse Recovery Charge	$Q_{rr}$		--	0.56	--	$\mu C$
Peak Reverse Recovery Current	$I_{rrm}$		--	9.3	--	A

**Notes**

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2.  $I_{AS} = 2.4A, V_{DD} = 50V, R_G = 25\Omega,$  Starting  $T_J = 25^\circ\text{C}$
3. Identical low side and high side switch with identical  $R_G$



Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 1. Output Characteristics

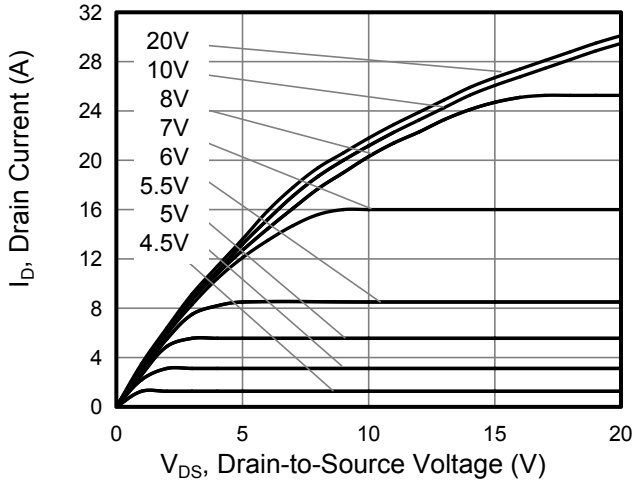


Figure 2. Transfer Characteristics

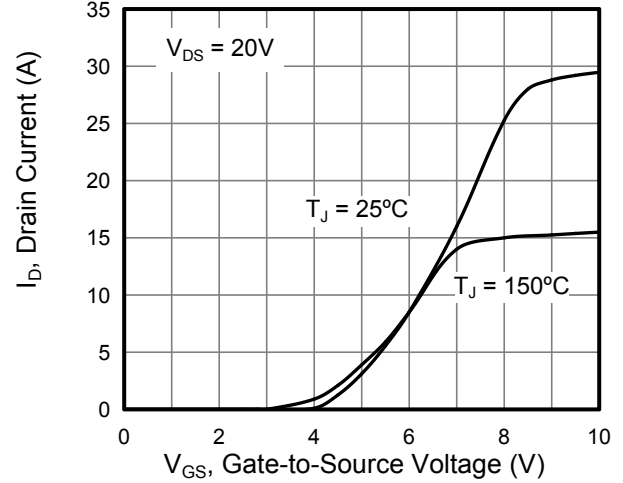


Figure 3. On-Resistance vs. Drain Current

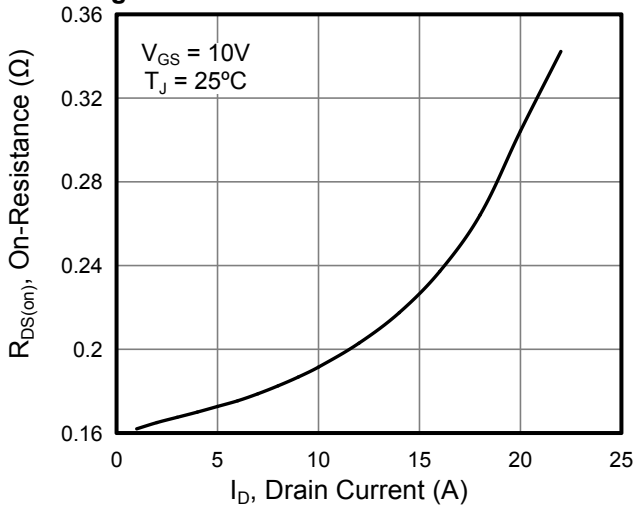


Figure 4. Capacitance

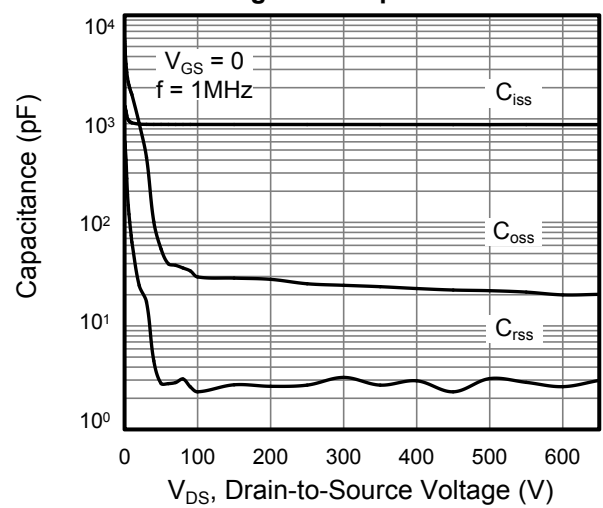


Figure 5. Gate Charge

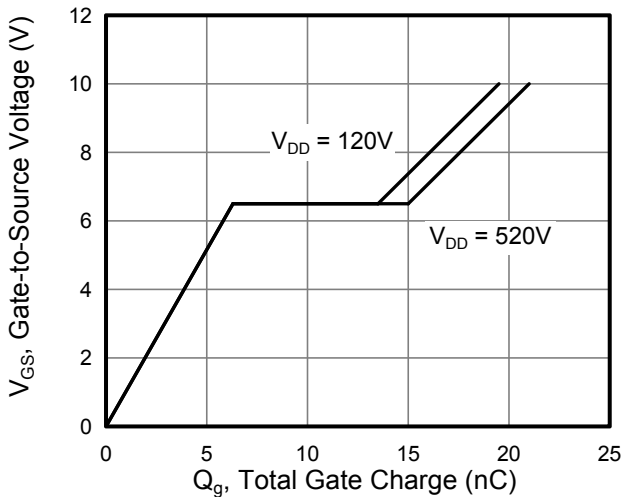
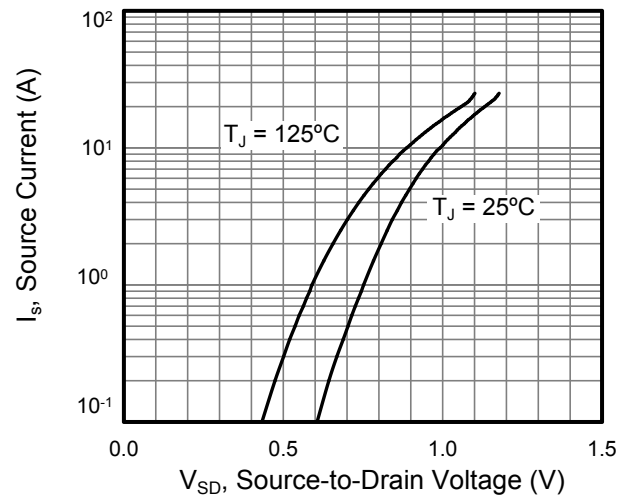


Figure 6. Body Diode Forward Voltage





Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 7. On-Resistance vs. Junction Temperature

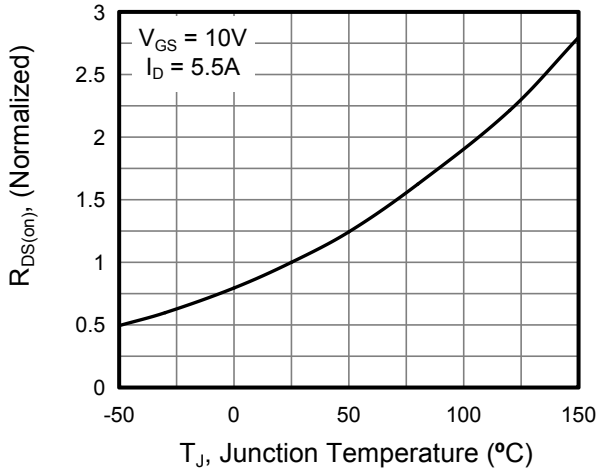


Figure 8. Breakdown voltage vs. Junction Temperature

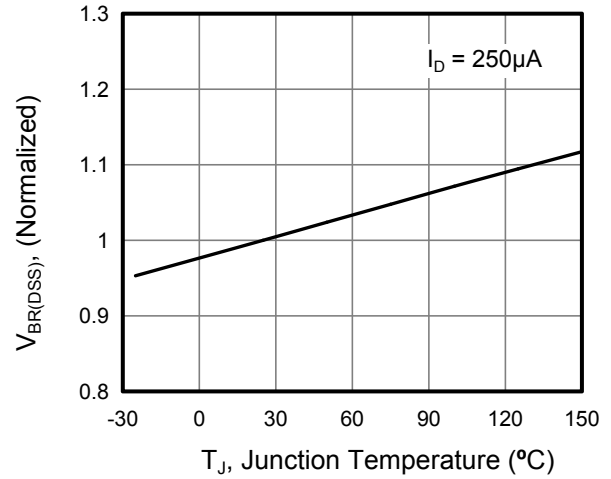


Figure 9. Transient Thermal Impedance TO-220F

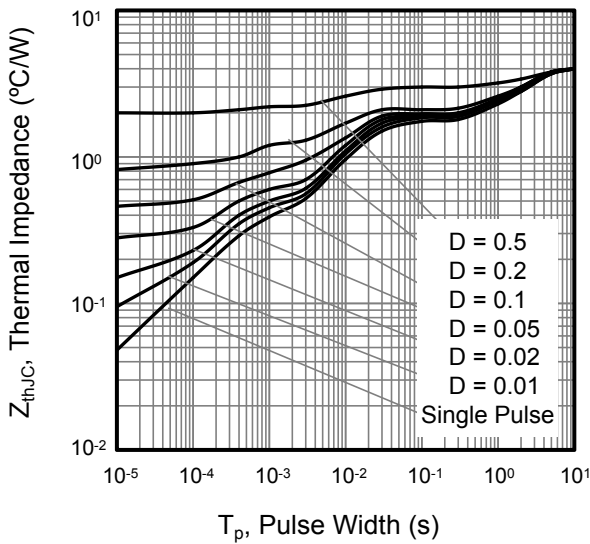


Figure 10. Safe operation area for TO-220F

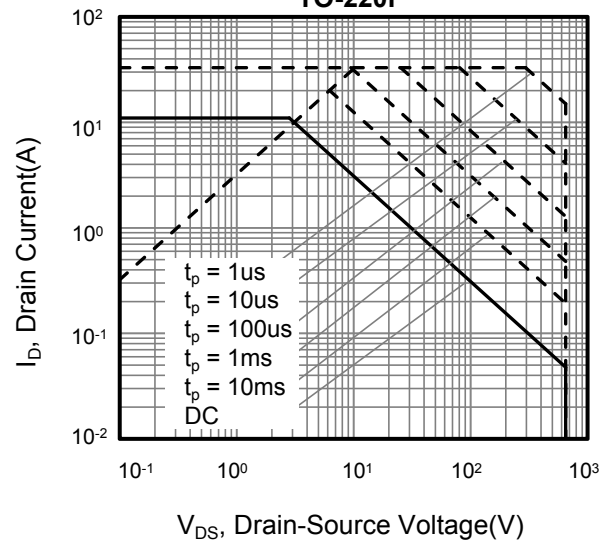




Figure A: Gate Charge Test Circuit and Waveform

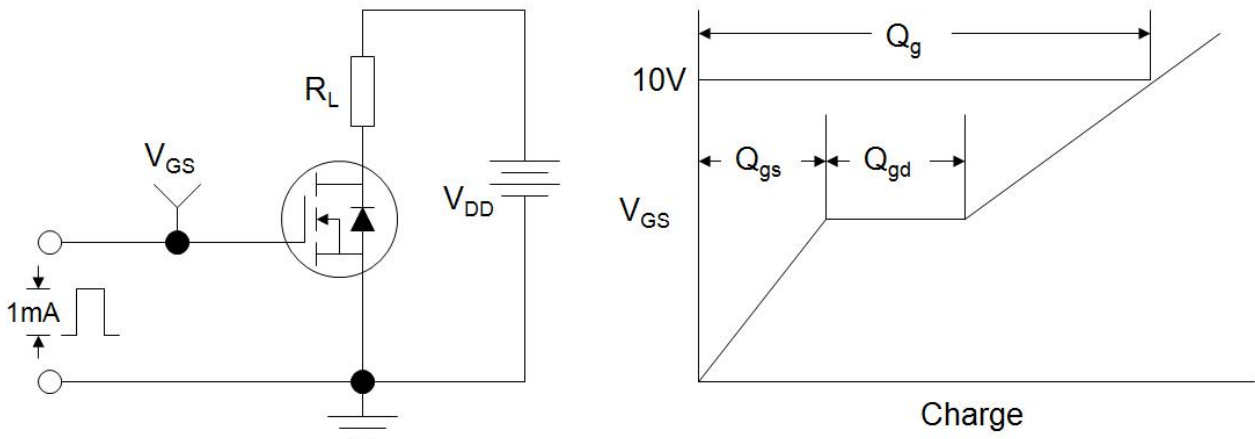


Figure B: Resistive Switching Test Circuit and Waveform

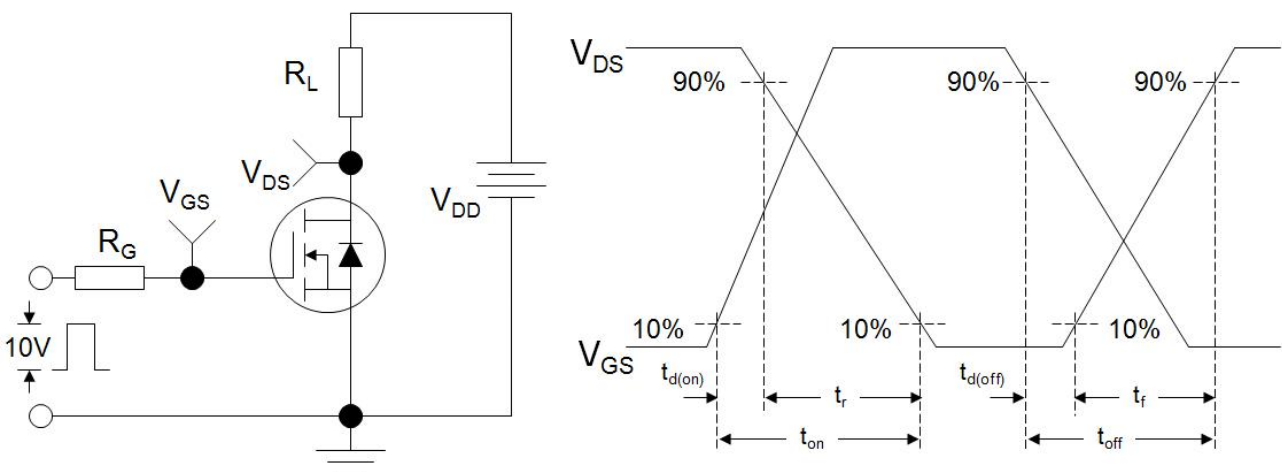
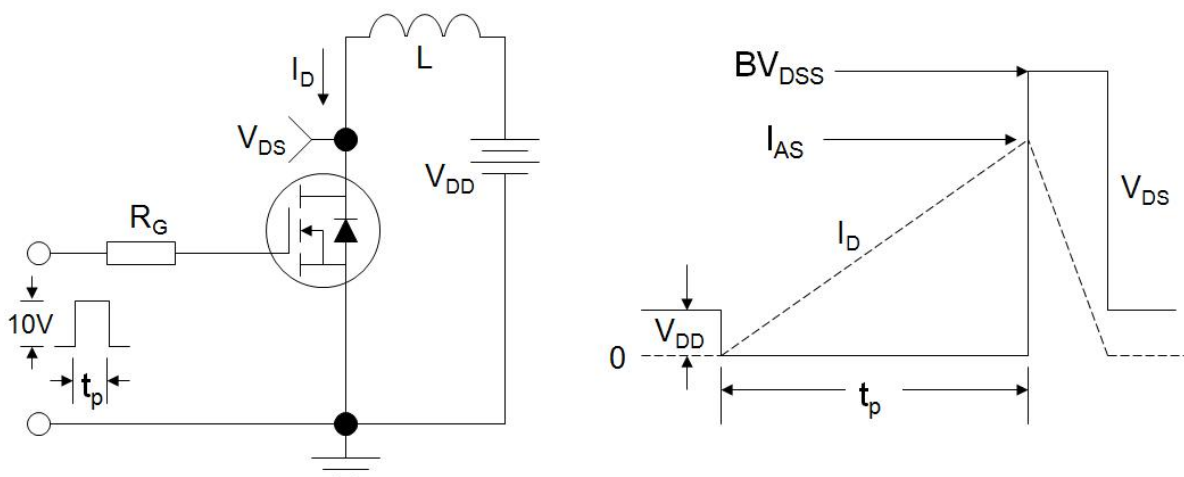
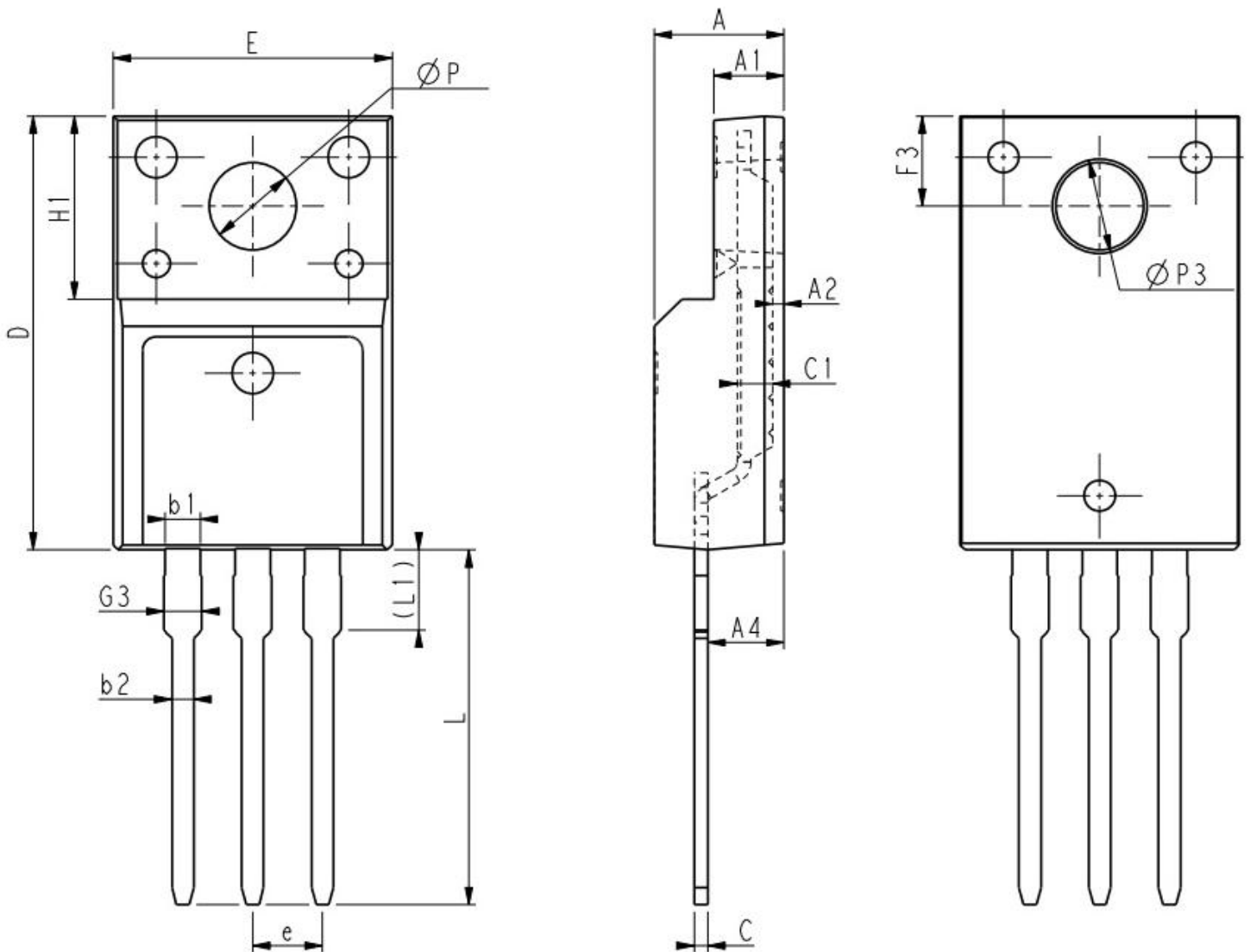


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





### TO-220F



Unit:mm			
Symbol	Min.	Nom	Max.
E	9.96	10.16	10.36
A	4.50	4.70	4.90
A1	2.34	2.54	2.74
A2	0.30	0.45	0.60
A4	2.56	2.76	2.96
c	0.40	0.50	0.65
c1	1.20	1.30	1.35
D	15.57	15.87	16.17
H1	6.70REF		

Unit:mm			
Symbol	Min.	Nom	Max.
e	2.54BSC		
L	12.68	12.98	13.28
L1	2.93	3.03	3.13
$\Phi P$	3.03	3.18	3.38
$\Phi P3$	3.15	3.45	3.65
F3	3.15	3.30	3.45
G3	1.25	1.35	1.55
b1	1.18	1.28	1.43
b2	0.70	0.80	0.95



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